Erratum: Lattice-dynamical calculation of phonon scattering at ideal Si-Ge interfaces [J. Appl. Phys. 97, 024903 (2005)]

H. Zhao and J. B. Freund
Department of Theoretical and Applied Mechanics,
University of Illinois at Urbana-Champaign,
Urbana, Illinois 61801

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Due to an error in the final phase of copy editing, the axes of all of the figures in the paper were mislabeled. The correctly labeled figures are provided here.

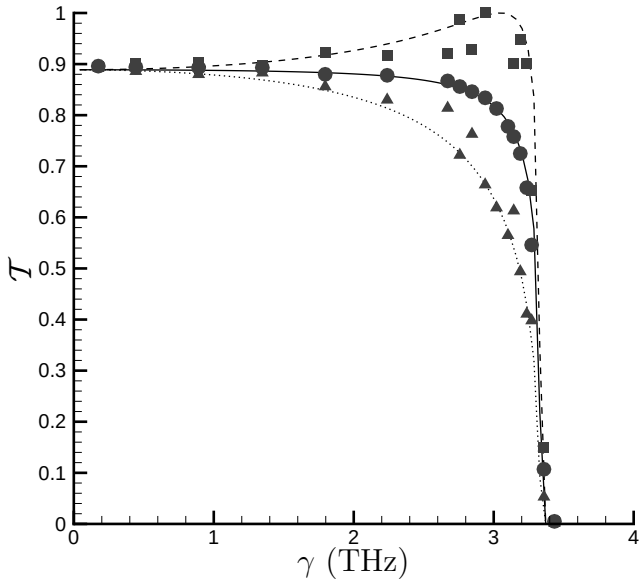

Figure 1: Transmission coefficients $\mathcal{T}$ of transverse phonons in the [100] direction: ——— , • average $\mathcal{T}$; - - - - , ■ maximal $\mathcal{T}$; ····· , ▲ minimal $\mathcal{T}$. Lines are the present semi-analytical results and symbols are from the wave packet computations of Schelling *et al.*

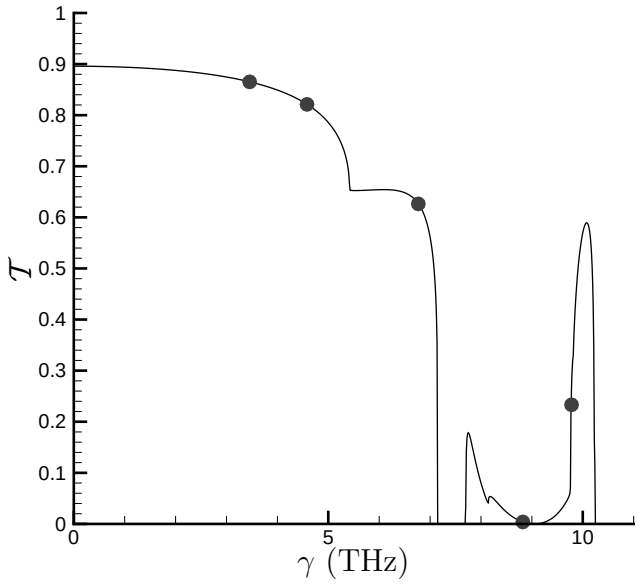

Figure 2: Transmission coefficients $\mathcal{T}$ of the non-degenerate branch of phonons in the [111] direction: —— present method; • wave packet method.

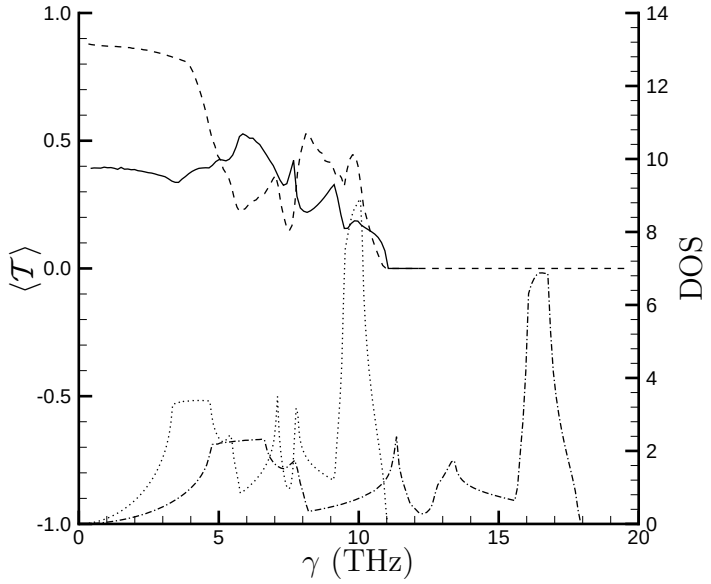

Figure 3: Average transmission coefficient $\langle \mathcal{T} \rangle$ and density of states (DOS) defined as the number of states per unit cell per THz: - - - - $\langle \mathcal{T} \rangle$ for Si→Ge; —— $\langle \mathcal{T} \rangle$ for Ge→Si; —·— DOS in Si (scaled by $10^{12}a^{-3}$); ····· DOS in Ge.

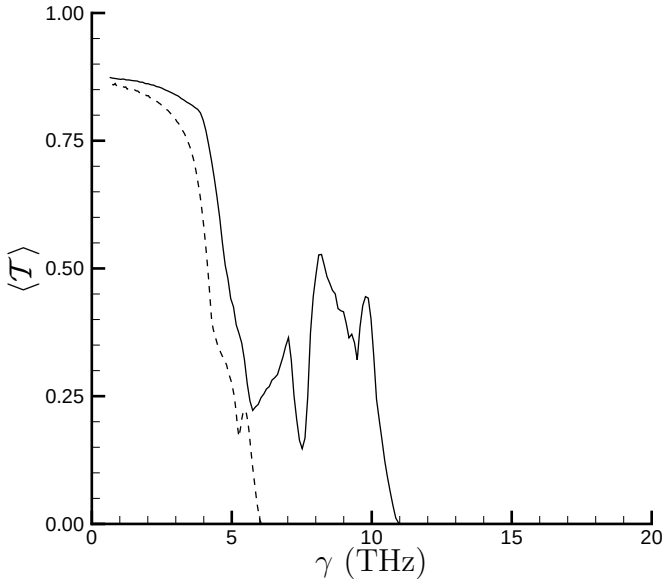

Figure 4: Average transmission coefficient $\langle \mathcal{T} \rangle$ of Si→Ge scattering based on a —— diamond cubic structure and a ---- fcc lattice model.

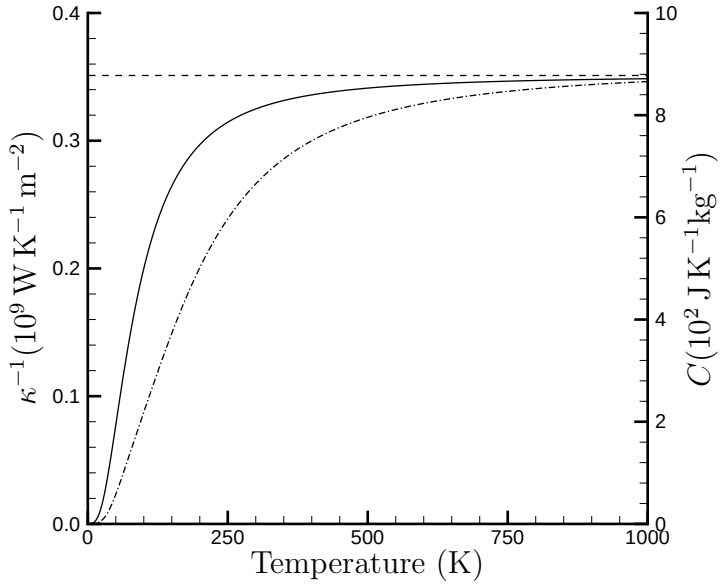

Figure 5: Dependence of Kapitza conductance κ^{-1} on temperature: —— Bose-Einstein distribution; ---- Boltzmann distribution; —·— specific heat of Si from linearized Stillinger-Weber potential.

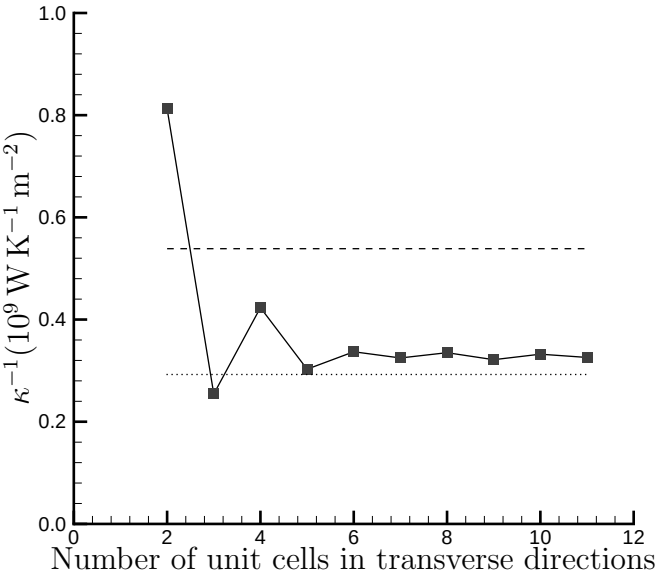

Figure 6: Dependence of the Kapitza conductance κ^{-1} on the transverse domain size at 300K: —— square cross section; - - - - 2×8 cross section; ····· 3×5 cross section.

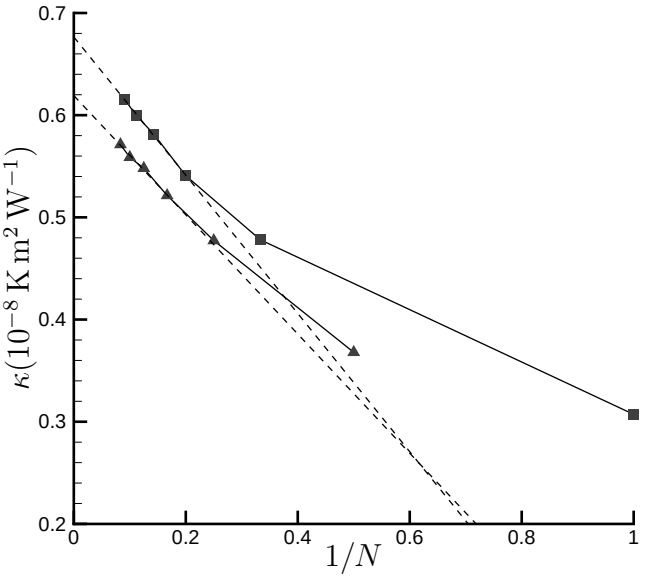

Figure 7: Dependence of the thermal resistance κ on the increasing number of interfaces N at 300K. Each layer is of 6 unit cells thick: ■ Si→Ge; ▲ Si→Si; ---- linear extrapolation.

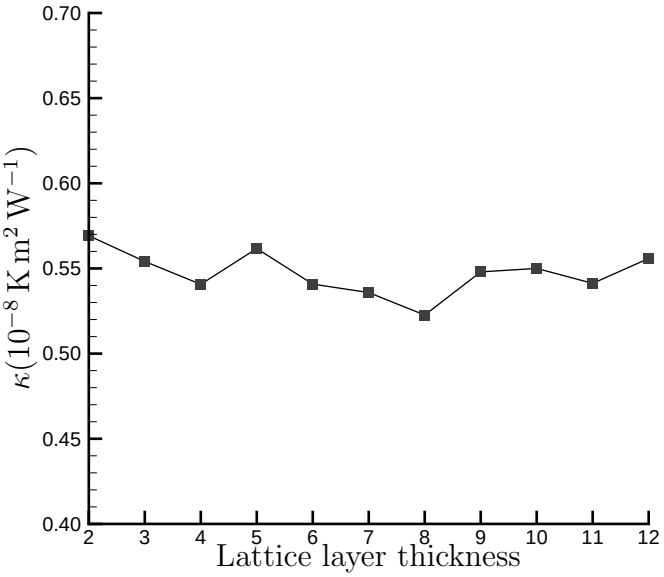

Figure 8: Dependence of the Kapitza resistance κ on the superlattice layer thickness at 300K for $N = 5$ interfaces.